

FEATURES

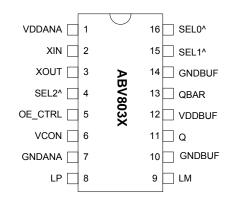
- Less than 0.4ps RMS (12KHz-20MHz) phase jitter for all frequencies.
- Less than 25ps (typ.) peak to peak jitter for all frequencies.
- Low phase noise output (@ 1MHz frequency offset
 - * -144dBc/Hz for 155.52MHz
 - -140dBC/Hz for 311.04MHz
- 19MHz-40MHz crystal input.
- 38MHz-320MHz output.
- Available in PECL, LVDS, or CMOS outputs.
- No external varicap required.
- Output Enable selector.
- Wide pull range (+/-200ppm).
- 3.3V operation.
- Available in 3x3 QFN or 16-pin TSSOP packages.

DESCRIPTION

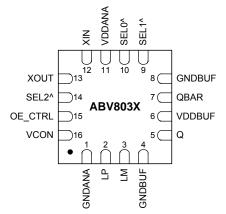
The ABV803X is a monolithic low jitter and low phase noise VCXO, capable of 0.4ps RMS phase jitter and CMOS, LVDS, or PECL outputs, covering a wide frequency output range up to 320MHz. It allows the control of the output frequency with an input voltage (VCON), using a low cost crystal. The frequency selector pads of ABV803X enable output frequencies of (2, 4, 8, or 16) * F_{XIN} . The ABV803X is designed to address the demanding requirements of high performance applications such as SONET, GPS, Video, etc.

BLOCK DIAGRAM



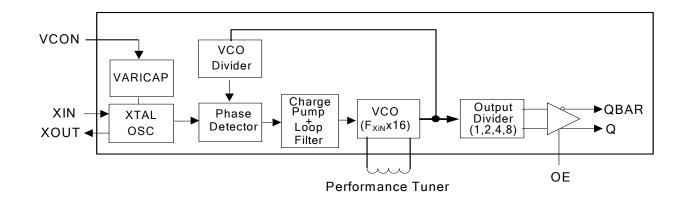






<u>3x3 QFN</u>

Note1: QBAR is used for single ended CMOS output. Note2: ^ Denotes internal pull up resistor.





OUTPUT ENABLE LOGICAL LEVELS

Part #	OE	State
ABV8038 (PECL)	0 (Default)	Output enabled
	1	Tri-state
ABV8037 & 39 (CMOS or CMOS)	0	Tri-state
ABV8037 & 39 (CMOS 01 CMOS)	1 (Default)	Output enabled

PIN DESCRIPTIONS

Name	TSSOP Pin number	3x3mm QFN Pin number	Туре	Description
VDDANA	1	11	Р	VDD for analog Circuitry.
XIN	2	12	I	Crystal input pin. (See Crystal Specifications on page 4).
XOUT	3	13	0	Crystal output pin. (See Crystal Specifications on page 4).
SEL2	4	14	Ι	Output frequency Selector pin.
OE_CTRL	5	15	Ι	Output enable control pin. (See OE_CTRL Logic Levels).
VCON	6	16	I	Voltage control input.
GNDANA	7	1	Р	Ground for analog circuitry.
LP	8	2	-	Tuning inductor connection. The inductor is recommended to be a high Q small size 0402 or 0603 SMD component, and must be
LM	9	3	-	placed between LP and adjacent LM pin. Place inductor as close to the IC as possible to minimize parasitic effects and to maintain inductor Q.
GNDBUF	10	4	Р	GND connection for output buffer circuitry.
Q	11	5	0	PECL or LVDS output.
VDDBUF	12	6	Ρ	VDD connection for output buffer circuitry. VDDBUF should be separately decoupled from other VDDs whenever possible.
QBAR	13	7	0	Complementary PECL, LVDS, Or single ended CMOS output.
GNDBUF	14	8	Р	GND connection for output buffer circuitry.
SEL1	15	9		Output frequency Selector pin.
SEL0	16	10		Output frequency Selector pin.



FREQUENCY SELECTION TABLE

SEL2	SEL1	SEL0	Selected Multiplier/Output Frequency
0	0	0	VCO Max*
0	0	1	VCO Min*
0	1	0	Reserved
0	1	1	Reserved
1	0	0	Fin x 2
1	0	1	Fin x 8
1	1	0	Fin x 16
1	1	1	Fin x 4

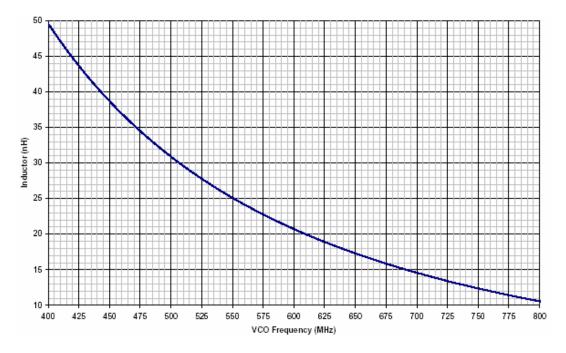
All SEL pads have internal pull-ups (default value is '1'). Bond to GND to set to 0.

* Special Test Modes to help selecting the inductor value for the target output frequency.

PERFORMANCE TUNING & INDUCTOR VALUE SELECTION

Please refer to Abracon's 'Tuning Assistant' software to automatically calculate the optimum inductor values for your application. In addition, the chart below could be used as a reference for quick inductor value selection. Please note that the inductor values mentioned in the table below, or when using the 'Tuning Assistant' are derived based on the parasitic values of Abracon's evaluation board. For performance enhancement of your custom board design, please follow the following instruction:

Use the special test modes "VCO Max" and "VCO Min" to determine the optimum inductor value. "VCO Max" represents the high end of the VCO range and "VCO Min" represents the low end of the VCO range. The output frequency in the "VCO Max" and "VCO Min" test modes is VCO/16. This means that the output frequencies are around the crystal frequency that will be used. The optimum inductor value is where the target crystal frequency is closest to the middle between the "VCO Max" and "VCO Min" output frequencies. In this case the VCO will lock in the middle of its tuning range with maximum margin on either side.





ELECTRICAL SPECIFICATIONS

1. Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage	Vdd		4.6	V
Input Voltage, dc	Vi	-0.5	V _{DD} +0.5	V
Output Voltage, dc	Vo	-0.5	V _{DD} +0.5	V
Storage Temperature	Ts	-65	150	°C
Ambient Operating Temperature*	TA	-40	85	°C
Junction Temperature	TJ		125	°C
Lead Temperature (soldering, 10s)			260	°C
ESD Protection, Human Body Model			2	kV

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

* Note: Operating Temperature is guaranteed by design for all parts (COMMERCIAL and INDUSTRIAL), but tested for COMMERCIAL grade only.

2. Crystal Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Crystal Resonator Frequency	Fxin	Parallel Fundamental Mode	19		40	MHz
		at VCON = 0V		17.7		
Crystal Loading Rating	CL (xtal)	at VCON = 1.65V		9.5		рF
		at VCON = 3.3V		5.4		
Crystal Pullability	C_0/C_1 (xtal)	AT cut			250	-
Recommended ESR	Re	AT cut			30	Ω

Note: Crystal Loading rating: The listed numbers are for the IC only. Specify the crystal for the value at VCON = 1.65V and add the PCB & package parasitic. A round number (i.e. 12pF) can be achieved by adding external capacitors. Try to add the same value to XIN and XOUT, and please note, that frequency pulling and oscillator gain may decrease.

3. Voltage Control Crystal Oscillator

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
VCXO Stabilization Time *	Тусхоятв	From power valid			10	ms
VCXO Tuning Range		$\begin{array}{l} {\sf F}_{XIN} = 19 - 40 {\sf MHz}; \\ {\sf XTAL} \ {\sf C}_0 / {\sf C}_1 < 250 \\ 0 {\sf V} \le {\sf VCON} \le 3.3 {\sf V} \end{array}$		500		ppm
CLK output pullability		VCON=1.65V, ±1.65V	±200			ppm
VCXO Tuning Characteristic				150		ppm/V
Pull range linearity					10	%
VCON pin input impedance			60	80		kΩ
VCON modulation BW		$0V \le VCON \le 3.3V$, -3dB	25			kHz

Note: Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits.



4. General Electrical Specifications

PARAMETERS	SYMBOL	CON	MIN.	TYP.	MAX.	UNITS	
Supply Current, Dynamic (with	IDD	PECL/LVDS/CMOS	38MHz <fout<100mhz< td=""><td></td><td></td><td>65/45/30</td><td>mA</td></fout<100mhz<>			65/45/30	mA
Loaded Outputs)	טטו		100MHz <fout<320mhz< td=""><td></td><td></td><td>80/60/40</td><td>IIIZA</td></fout<320mhz<>			80/60/40	IIIZA
Operating Voltage	Vdd			2.97		3.63	V
Output Clock Duty Cycle		@ 50% V _{DD} (CMOS) @ 1.25V (LVDS) @ V _{DD} – 1.3V (PECL)	45 45 45	50 50 50	55 55 55	%
Short Circuit Current					±50		mA

Note: CMOS operation is not advised above 200MHz with 15pF load; and 320MHz with 10pF load.

5. Jitter Specifications

PARAMETERS	CONDITIONS	FREQUENCY	MIN.	TYP.	MAX.	UNITS
Integrated jitter DMS	Integrated 12 kHz to 20 MHz	155.52MHz		0.4	0.5	2
Integrated jitter RMS		311.04MHz		0.4	0.5	ps
	With capacitive decoupling	77.76MHz		2.5	4	
Period jitter RMS	between VDD and GND.	155.52MHz		3	5	ps
	Over 10,000 cycles.	311.04MHz		4	7	
	With capacitive decoupling	77.76MHz		18	30	
Period jitter Peak-to- Peak	between VDD and GND.	155.52MHz		20	30	ps
	Over 10,000 cycles.	311.04MHz		25	35	

6. Phase Noise Specifications

PARAMETERS	FREQ.	@10Hz	@100Hz	@1kHz	@10kHz	@100kHz	@1M	@10M	UNITS
Phase Noise	77.76MHz	-66	-96	-124	-134	-132	-145	-149	
relative to	155.52MHz	-62	-92	-120	-132	-128	-144	-150	dBc/Hz
carrier (typical)	311.04MHz	-59	-86	-116	-129	-124	-140	-148	

Note: Phase Noise measured at VCON = 0V.

7. CMOS Electrical Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output drive current	Іон	V_{OH} = V_{DD} -0.4V, V_{DD} =3.3V	30			mA
	Iol	$V_{OL} = 0.4V, V_{DD} = 3.3V$	30			mA
Output Clock Rise/Fall Time		0.3V ~ 3.0V with 15 pF load		0.7		ns
Output Clock Rise/Fall Time		20%-80% with 50 Ω Load		0.3		ns

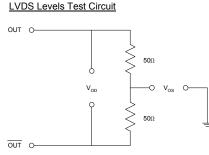


8. LVDS Electrical Characteristics

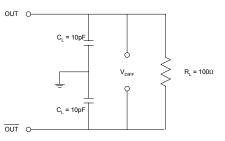
PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Differential Voltage	Vod		247	355	454	mV
VDD Magnitude Change	ΔV_OD		-50		50	mV
Output High Voltage	Vон	R_L = 100 Ω		1.4	1.6	V
Output Low Voltage	Vol	(see figure)	0.9	1.1		V
Offset Voltage	Vos		1.125	1.2	1.375	V
Offset Magnitude Change	ΔV os		0	3	25	mV
Power-off Leakage	Ioxd	$V_{out} = V_{DD} \text{ or } GND$ $V_{DD} = 0V$		±1	±10	uA
Output Short Circuit Current	I _{OSD}			-5.7	-8	mA

9. LVDS Switching Characteristics

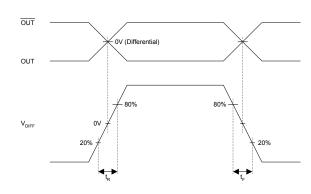
PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Differential Clock Rise Time	tr	R _L = 100 Ω	0.2	0.7	1.0	ns
Differential Clock Fall Time	tf	C∟ = 10 pF (see figure)	0.2	0.7	1.0	ns



LVDS Switching Test Circuit



LVDS Transistion Time Waveform



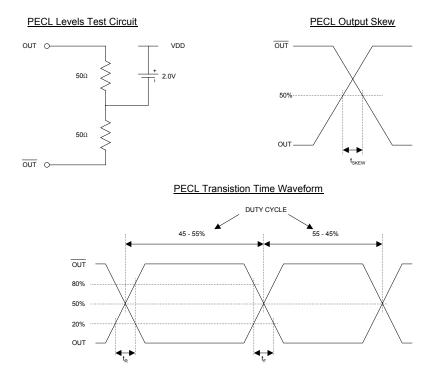


10. PECL Electrical Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
Output High Voltage	Vон	R_L = 50 Ω to (V _{DD} – 2V)	V _{DD} - 1.025		V
Output Low Voltage	Vol	(see figure)		V _{DD} - 1.620	V

11. PECL Switching Characteristics

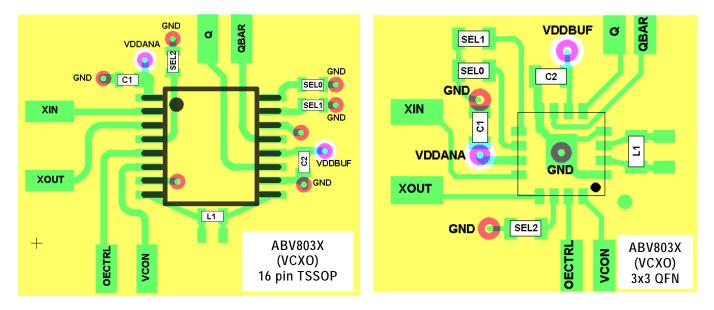
PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Clock Rise Time	tr	@20/80% - PECL		0.6	1.5	ns
Clock Fall Time	t _f	@80/20% - PECL		0.5	1.5	ns



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LAYOUT RECOMMENDATIONS



PCB LAYOUT CONSIDERATIONS FOR PERFORMANCE OPTIMIZATION

The following guidelines are to assist you with a performance optimized PCB design:

- Keep all the PCB traces to ABV80 as short as possible, as well as keeping all other traces as far away from it as possible.
- Place the crystal as close as possible to both crystal pins of the device. This will reduce the cross-talk between the crystal and the other signals.
- Separate crystal pin traces from the other signals on the PCB, but allow ample distance between the two crystal pin traces.
- Place a 0.01µF~0.1µF decoupling capacitor between VDD and GND, on the component side of the PCB, close to the VDD pin. It is not recommended to place this component on the backside of the PCB. Going through vias will reduce the signal integrity, causing additional jitter and phase noise.

- It is highly recommended to keep the VDD and GND traces as short as possible.
- When connecting long traces (> 1 inch) to a CMOS output, it is important to design the traces as a transmission line or 'stripline', to avoid reflections or ringing. In this case, the CMOS output needs to be matched to the trace impedance. Usually 'striplines' are designed for 50Ω impedance and CMOS outputs usually have lower than 50Ω impedance so matching can be achieved by adding a resistor in series with the CMOS output pin to the 'stripline' trace.
- Please contact Abracon for the application note on how to design outputs driving long traces or the Gerber files for the ABV80 layout.

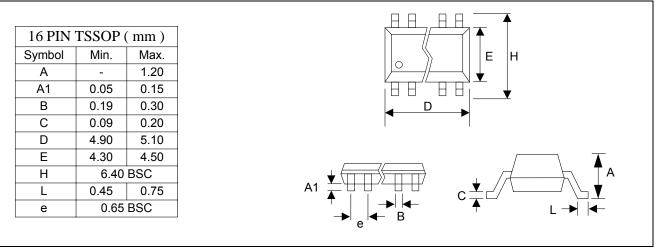


(Preliminary) ABV8037/38/39

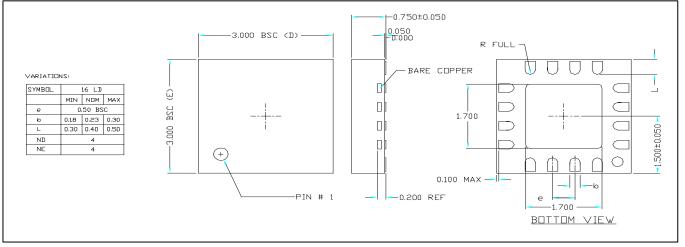
38MHz-320MHz Low Phase Noise VCXO

PACKAGE INFORMATION

16-PIN SSOP

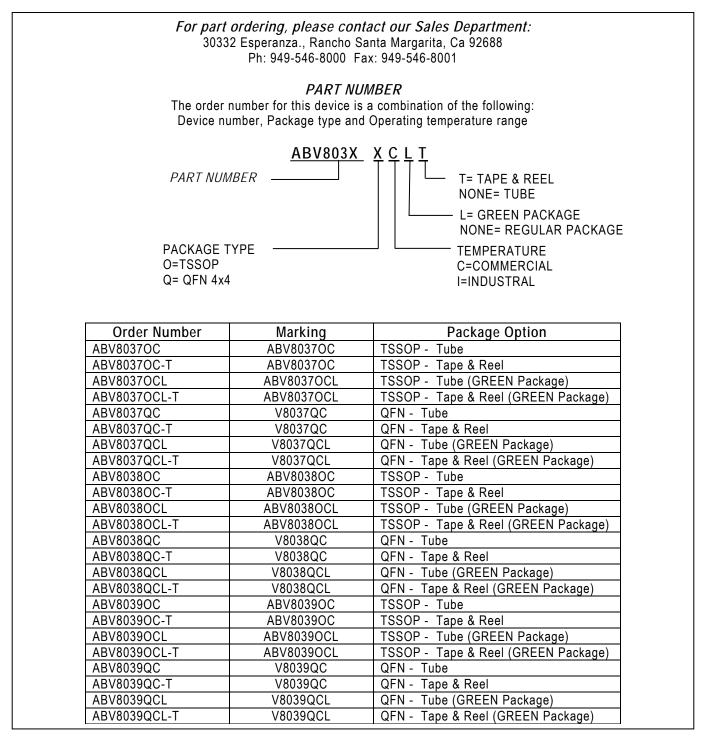


16-PIN 3x3 QFN





ORDERING INFORMATION



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